

FEATURES

Fast	response,	instantly	clamping	the tra	ansient c	ver voltage.
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- High surge current handling capability.
- High energy absorption capability.
- Low clamping voltages, providing better surge protection.
- Low capacitance values, providing digital switching circuitryprotection.
- High insulation resistance, preventing electric arcing to the adjacent

devices or circuits.



APPROVALS

RoHS	Compliance with 2011/65/EU
HF	Compliance with IEC61249-2-21:2003

APPLICATIONS

Mobile communication.

- Computer/DSP product.
- Video and audio ports.

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- Portable/Hand-Held Products.
- Data, Diagnostic I/O ports.

ELECTRICAL SPECIFICATION

Test condition				
Varistor voltage	In = 1 mA DC			
Leakage current	Vdc = 12 V DC			
Maximum clamping voltage	lc = 1 A			
Rated peak single pulse transient current	8 / 20 µs waveform, +/- each 1 time induce			
Capacitance	10/1000 µs waveform			
Insulation resistance after reflow soldering	f = 1MHz, Vrms = 0.5 V			



ELECTRICAL SPECIFICATION

Electrical specification				
Maximum allowable continuous DC voltage	12	V		
trigger voltage / Varistor voltage / breakdown voltage	110-150	V		
Maximum clamping voltage	200	V	Maximum	
Rated peak single pulse transient current	1	А	Maximum	
Nonlinearity coefficient	> 12			
Leakage current at continuous DC voltage	< 0.1	uA		
Response time	< 0.5	ns		
Varistor voltage temperature coefficient	< 0.05	%/°C		
Capacitance measured at 1MHz	3.0	pF	Typical	
Capacitance tolerance	-50 to +50	%		
Insulation resistance after reflow soldering on PCB	> 10	MΩ		
Operating ambient temperature	-55 to +125	°C		
Storage temperature	-55 to +125	°C		



RELIABILITY TESTING PROCEDURES

Reliability parameter		Test methods and remarks	Test requirement
Pulse current capability	lmax 8/20 µs	IEC 1051-1, Test 4.5. 10 pulses in the same direction at 2 pulses per minute at maximum peak current	d Vn ∕Vn≤10% no visible damage
Electrostatic discharge capability	ESD C=150 pF, R=330Ω	IEC 1000-4-2 Each 10 times in positive/negative direction in 10 sec at 8KV contact discharge (Level 4)	d Vn ∕Vn≤10% no visible damage
	Thermal shock	IEC 68-2-14 Condition for 1 cycle Step 1 : Min. –40 °C , 30±3 min. Step 2 : Max. +125 °C , 30±3 min. Number of cycles: 30 times	d Vn ∕Vn≤5% no visible damage
	Low temperature	IEC 68-2-1 Place the chip at -40±5 °C for 1000±12hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤5% no visible damage
Environmenta	High temperature	IEC 68-2-2 Place the chip at 125±5 °C for 1000± 24hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤5% no visible damage
l reliability	Heat resistance	IEC 68-2-3 Apply the rated voltage for 1000±48hrs at 85±3 [°] C. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤5% no visible damage
	Humidity resistance	IEC 68-2-30 Place the chip at 40±2°C and 90 to 95% humidity for 1000±24hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤5% no visible damage
	Pressure cooker test	Place the chip at 2 atm, 120 $^\circ$ C, 85%RH for 60 hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤10% no visible damage
	Operating life	Apply the rated voltage for 1000±48hrs at 125±3°C. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤10% no visible damage
Mechanical Reliability	Adhesive strength	IEC 68-2-22 Applied force on SMD chip by fracture from PCB	Strength>10 N no visible damage



T(mm)

≤ 0.6

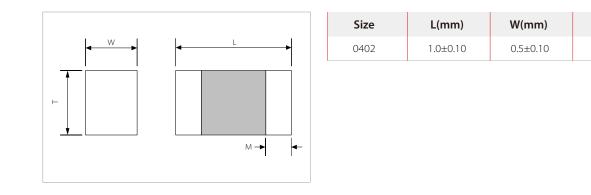
M(mm)

0.20±0.10

MATERIAL SPECIFICATION

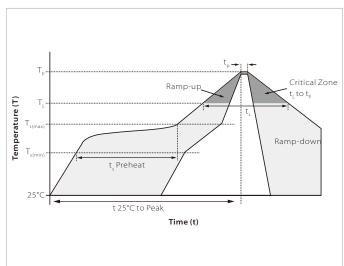
Body	Internal electrode	External electrode	Thickness of Ni/Sn plating layer
ZnO based ceramics	Silver – Palladium	Silver – Nickel – Tin	Nickel > 1 μ m, Tin > 2 μ m

DIMENSION SPECIFICATION



SOLDERING RECOMMENDATIONS

Reflow Condition		Lead-free assembly	
	Temperature Max (T _{s(min)})	150°C	
Pre Heat	Temperature Max (T _{s(max)})	200°C	
	Time (min to max) (t_s)	60 – 180 secs	
Average ramp up rate (Liquidus Temp (T_L) to peak		3°C/second max	
T _{s(max)} to T _L - Ramp-up Rate		3°C/second max	
Reflow	Temperature (T _L) (Liquidus)	217°C	
Reliow	Time (min to max) (t _{$l)$}	60 – 150 seconds	
Peak Temperature (T _p)		260°C	
Time within 5°C of actual peak Temperature (t _p)		20 – 40 seconds	
Ramp-down Rate		6°C/second max	
Time 25°C to peak Temperature (T $_{_{P}}$)		8 minutes max.	
Do not exceed		260°C	





DRDERING INF ORMATIOON

Part Number	Package&Size	QTY/Reel	Reel Size
SME0402B12MA	0402 (1.0 x 0.5 mm)	10000PCS	7"



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